Ordering number: EN2267B

PNP/NPN Epitaxial Planar Type Silicon Transistors



## 2SB1271/2SD1907

# **High-Current Switching Applications**

## **Applications**

 Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications.

### **Features**

- · Suitable for sets whose height is restricted.
- · Low collector to emitter saturation voltage.
- · Large current capacity.

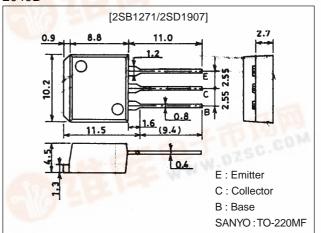
(): 2SB1271

## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

## **Package Dimensions**

unit:mm 2049B



Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)90	V
Collector-to-Emitter Voltage	VCEO		(–)80	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)6	V
Collector Current	I <sub>C</sub>	Name of the latest and the latest an	(-)7	Α
Collector Current (Pulse)	I <sub>CP</sub>	1 1 th 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	(–)12	А
Collector Dissipation	PC	A LITE LESS	1.65	W
		Tc=25°C	40	W
Junction Temperature	Tj	-101 (8)///	150	°C
Storage Temperature	Tstg	DEN	-55 to +150	°C

### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	UTIIL
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)80V, I <sub>E</sub> =0			(-)0.1	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(-)0.1	mA
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)1A	70*	- 11	280*	-014
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)2V, I <sub>C</sub> =(-)4A	30		50.	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A	W 160	20		MHz
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =(-)4A, I <sub>B</sub> =(-)0.4A			0.4	V
					(-0.5)	V

\*: The 2SB1271/2SD1907 are classified by 1A h<sub>FE</sub> as follows:

70 Q 140 100 R 200 140 S 280

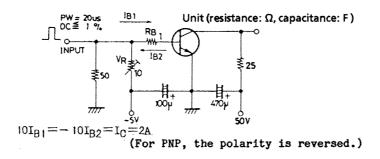
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- SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges,or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

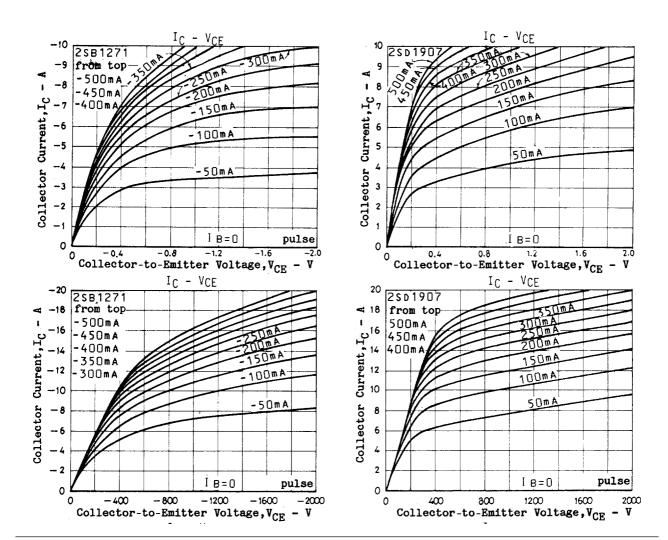
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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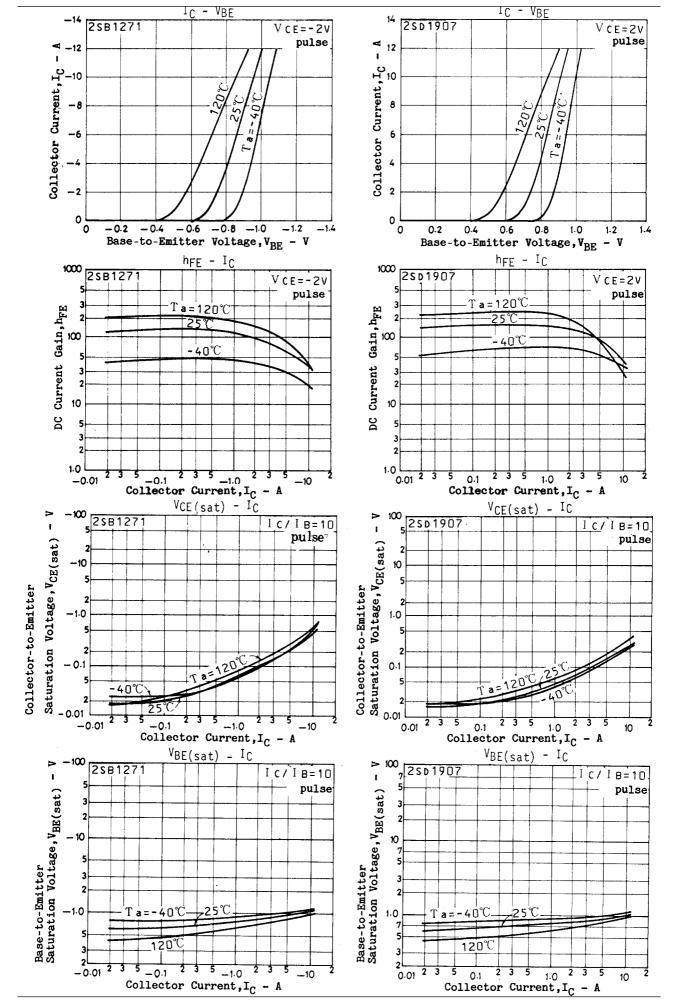
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	O IIII
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)1mA, I <sub>E</sub> =0	(–)90			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(–)80			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)1mA, I <sub>C</sub> =0	(–)6			V
Turn-ON Time	ton	See specified test circuit.		(0.2)		μs
				0.1		μs
Storage Time	t <sub>stg</sub>	See specified test circuit.		(0.7)		μs
				1.6		μs
Fall Time	t <sub>f</sub>	See specified test circuit.		(0.2)		μs
				0.4		μs

### **Switching Time Test Circuit**

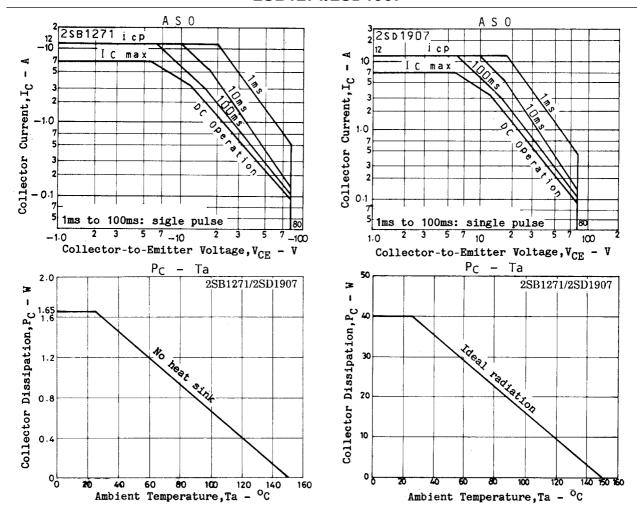




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